HIGH-VOLTAGE HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 100 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications
- Higher-Voltage Versions of ULN2003A and ULN2004A, for Commercial Temperature Range

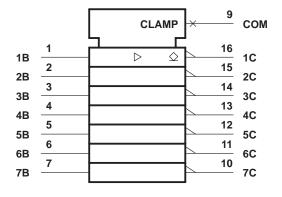
DORNPACKAGE (TOP VIEW) 1B 16 1 1C 2B ∏ 2 15 2C 3В П 14 T 3C 3 4B 4 13 Π 4C 12 7 5C 5В П 5 6В П 6 11 1 6C 10 7 7C 7В П 7 9 ПСОМ Ε 8

description

The SN75468 and SN75469 are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven npn Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of each Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

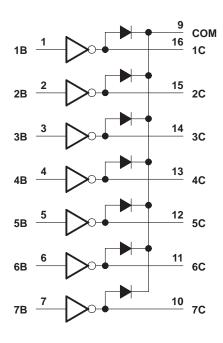
The SN75468 has a 2700- Ω series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS. The SN75469 has a 10.5-k Ω series base resistor to allow its operation directly with CMOS or PMOS that use supply voltages of 6 to 15 V. The required input current is below that of the SN75468.

logic symbol†



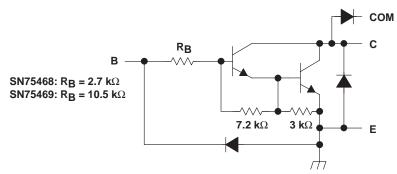
† This symbol is in accordance with ANSI/IEEE Std91-1984 and IEC publication 617-12.

logic diagram





schematic (each Darlington pair)



All resistor values shown are nominal.

absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-emitter voltage, V _{CE}	100 V
Input voltage, V _I (see Note 1)	30 V
Peak collector current (see Figures 14 and 15)	500 mA
Output clamp current, IOK	500 mA
Total emitter-terminal current	2.5 A
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

DISSIPATION RATING TABLE

PACKAGE T _A ≤ 25°C POWER RATING		DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING		
D	950 mW	7.6 mW/°C	608 mW		
N	1150 mW	9.2 mW/°C	736 mW		



electrical characteristics, $T_A = 25$ °C (unless otherwise noted)

PARAMETER		TEST TEST CONDI		NDITIONS	SN75468			SN75469			UNIT
		FIGURE	TEST CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VI(on)	On-state input voltage	5	V _{CE} = 2 V	I _C = 125 mA						5	V
				I _C = 200 mA			2.4			6	
				I _C = 250 mA			2.7				
				I _C = 275 mA						7	
				$I_C = 300 \text{ mA}$			3				
				$I_C = 350 \text{ mA}$						8	
	0 11 / 11		$I_{\parallel} = 250 \ \mu\text{A},$	$I_C = 100 \text{ mA}$		0.9	1.1		0.9	1.1	V
VCE(sat)	Collector-emitter saturation voltage	6	ΙΙ = 350 μΑ,	I _C = 200 mA		1	1.3		1	1.3	
			$I_I = 500 \mu A$,	I _C = 350 mA		1.2	1.6		1.2	1.6	
VF	Clamp-diode forward voltage	8	IF = 350 mA			1.7	2		1.7	2	V
	Collector cutoff current	1	V _{CE} = 100 V,	I _I = 0			50			50	
ICEX			V _{CE} = 100 V,	I _I = 0			100			100	μΑ
		2	T _A = 70°C	V _I = 1 V						500	
I(off)	Off-state input current	3	V _{CE} = 50 V, T _A = 70°C	$I_C = 500 \mu A$,	50	65		50	65		μΑ
	Input current	4	V _I = 3.85 V			0.93	1.35				
l _l			V _I = 5 V						0.35	0.5	mA
			V _I = 12 V						1	1.45	
	Clamp-diode reverse current	7	V _R = 100 V				50			50	
^I R			$V_R = 100 V$,	T _A = 70°C			100			100	μΑ
Ci	Input capacitance		$V_{ } = 0,$	f = 1 MHz		15	25		15	25	pF

switching characteristics, $T_A = 25^{\circ}C$ free-air temperature

	PARAMETER	Т	MIN	TYP	MAX	UNIT		
tPLH	Propagation delay time, low-to-high-level output	, ,	$R_L = 163 \Omega$,	$C_L = 15 pF$,		0.25	1	μs
^t PHL	Propagation delay time, high-to-low-level output	See Figure 9				0.25	1	μs
Vон	High-level output voltage after switching	$V_S = 50 V$,	$I_O \approx 300 \text{ mA},$	See Figure 10	V _S −20			mV

PARAMETER MEASUREMENT INFORMATION

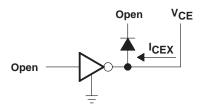


Figure 1. I_{CEX}

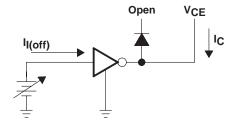


Figure 3. I_{I(off)}

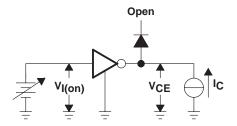


Figure 5. V_{I(on)}

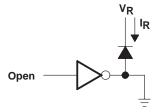


Figure 7. I_R

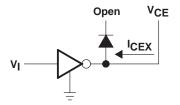


Figure 2. I_{CEX}

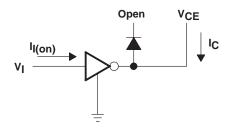
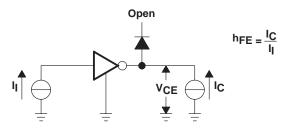


Figure 4. I_I



NOTE: I_I is fixed for measuring V_{CE(sat)}, variable for measuring h_{FE}.

Figure 6. h_{FE}, V_{CE(sat)}

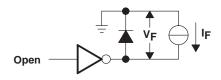


Figure 8. V_F

PARAMETER MEASUREMENT INFORMATION

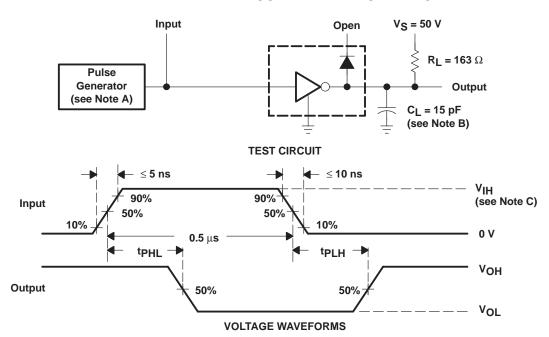


Figure 9. Test Circuit and Voltage Waveforms

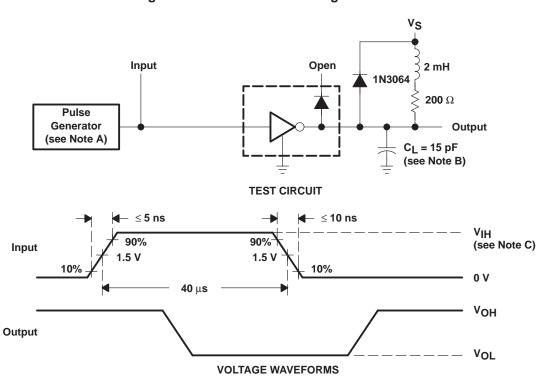


Figure 10. Latch-Up Test Circuit and Voltage Waveforms

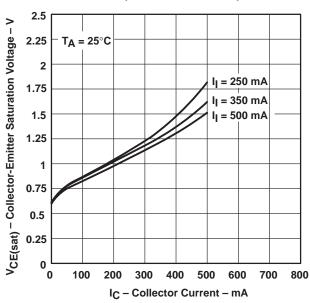
NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 Ω .

- B. C_L includes probe and jig capacitance.
- C. For testing the '468, $V_{IH} = 3 \text{ V}$; for the '469, $V_{IH} = 8 \text{ V}$.



TYPICAL CHARACTERISTICS

COLLECTOR-EMITTER
SATURATION VOLTAGE
vs
COLLECTOR CURRENT
(ONE DARLINGTON)



COLLECTOR-EMITTER
SATURATION VOLTAGE
vs
COLLECTOR CURRENT
(TWO DARLINGTONS PARALLELED)

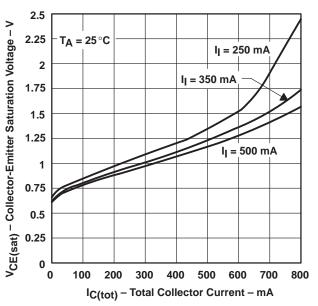
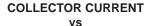
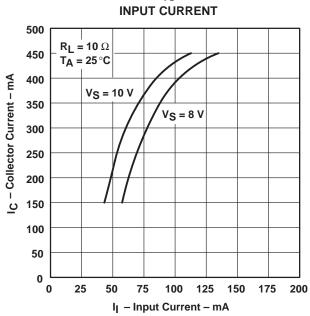


Figure 11

Figure 12





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Figure 13

THERMAL INFORMATION

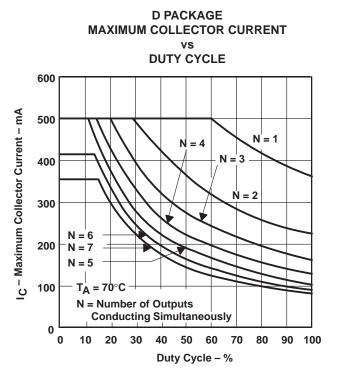


Figure 14

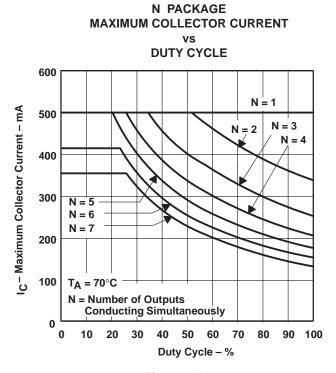


Figure 15

APPLICATION INFORMATION

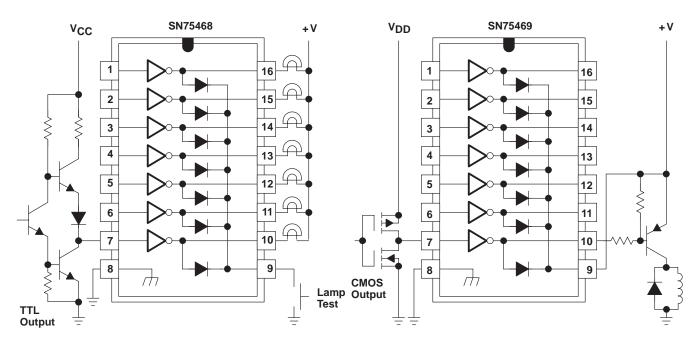


Figure 16. TTL to Load

Figure 17. Buffer for Higher Current Loads

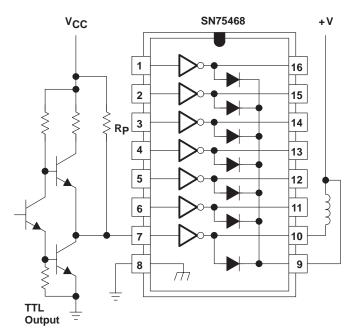


Figure 18. Use of Pullup Resistors to Increase Drive Current

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